MA795

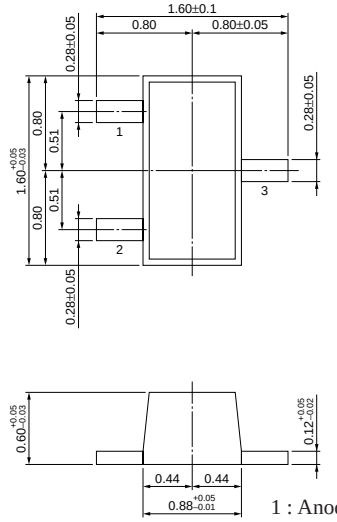
Silicon epitaxial planer type

For the switching circuit

■ Features

- Extra-small SS-Mini type 3-pin package, enabling high-density mounting
- Low forward voltage V_F, optimum for voltage rectification (Low V_F type of MA704A)
- Fast reverse recovery time t_{rr}, optimum for high-frequency rectification

Unit : mm



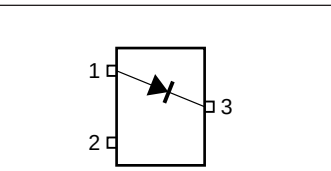
1 : Anode
2 : NC
3 : Cathode
SS-Mini Type Package (3-pin)

Marking Symbol : M2M

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Peak reverse voltage	V_{RM}	30	V
Forward current (DC)	I_F	30	mA
Peak forward current	I_{FM}	150	mA
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	– 55 to +125	˚C

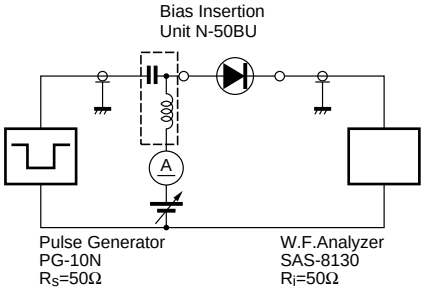
■ Internal Connection

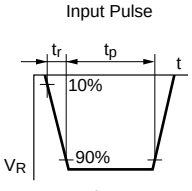


■ Electrical Characteristics (Ta= 25˚C)

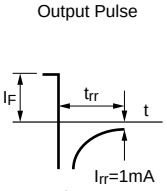
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 30V			30	µA
Forward voltage (DC)	V_{F1}	I_F=1mA			0.3	V
	V_{F2}	I_F= 30mA			1	V
Terminal capacitance	C_t	V_R =1V, f=1MHz		1.5		pF
Reverse recovery time	t_{rr}*	I_F = I_R=10mA I_{rr}= 1mA , R_L=100Ω		1		ns
Detection efficiency	η	V_{in}= 3$V_{(peak)}$, f= 30MHz R_L= 3.9kΩ, C_L=10pF		65		%

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 2000MHz
3. * t_{rr} measuring circuit





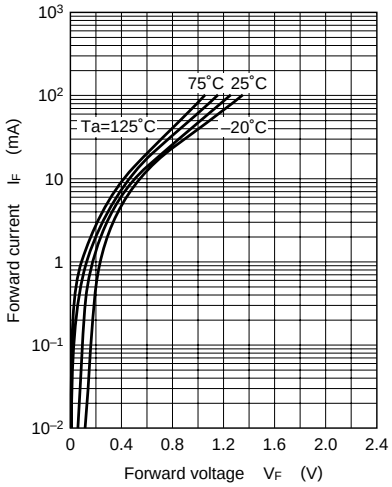
tp=2µs
tr=0.35ns
δ=0.05



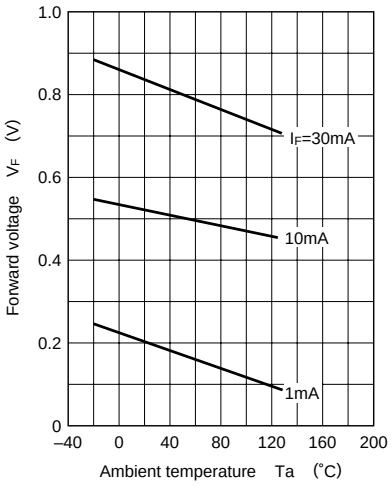
IF=10mA
IR=10mA
RL=100Ω

■ Marking

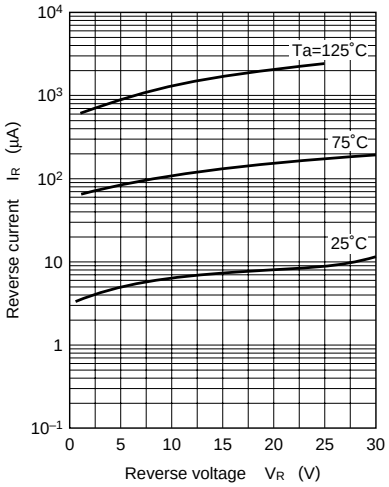
$I_F - V_F$



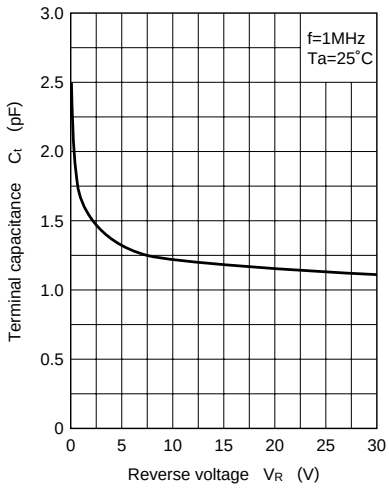
$V_F - Ta$



$I_R - V_R$



$C_t - V_R$



$I_R - Ta$